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Title:Pockels effect based fully integrated, strained silicon electro-optic modulator

Authors:Chmielak, Bartos (1); Waldow, Michael (1); Matheisen, Christopher (1); Ripperda, Christian (1); Bolten, Jens (2); Wahlbrink, Thorsten (2); Nagel, Michael (2); Merget, Florian (1); Kurz, Heinrich (1)

Author affiliation:(1) Institute of Semiconductor Electronics (IHT), RWTH Aachen University, Sommerfeldstrae 24, 52074 Aachen, Germany; (2) AMO GmbH, Otto-Blumenthal-Strae 25, 52074 Aachen, Germany

Corresponding author: Chmielak, B.(chmielak@iht.rwth-aachen.de)

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Abstract: We demonstrate for the first time a fully integrated electro-optic modulator based on locally strained silicon rib-waveguides. By depositing a Si3N4 strain layer directly on top of the silicon waveguide the silicon crystal is asymmetrically distorted. Thus its inversion symmetry is broken and a linear electro-optic effect is induced. Electro-optic characterization yields a record high value  $\chi(2)yyz = 122$  pm/V for the second-order susceptibility of the strained silicon waveguide and a strict linear dependence between the applied modulation voltage Vmod and the resulting effective index change  $\Delta$ neff. Spatially resolved micro-Raman and terahertz (THz) difference frequency generation (DFG) experiments provide in-depth insight into the origin of the electro-optic effect by correlating the local strain distribution with the observed second-order optical activity.